

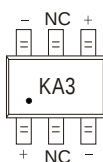
Plastic-Encapsulate Transistors

MMBD4448DW Switching Diode

FEATURES

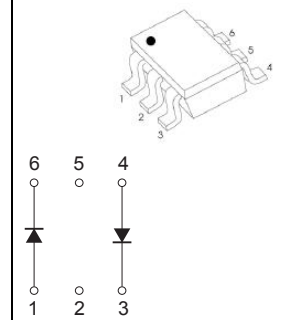
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance Power Dissipation

MARKING:KA3



Solid dot = Pin1 indicate.

SOT-363



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25 °C

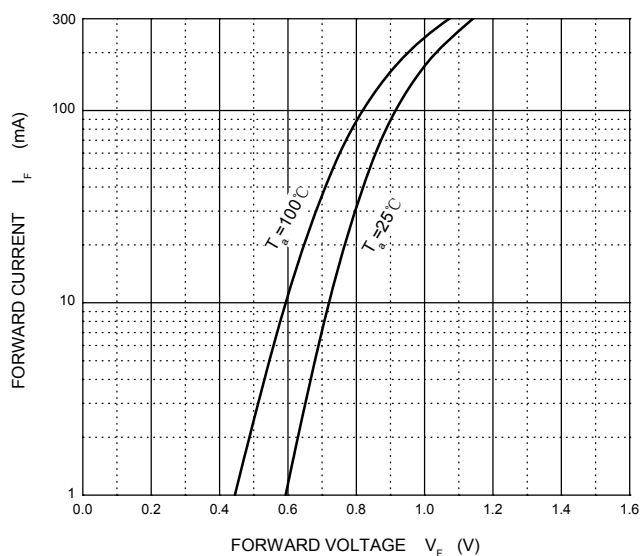
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	250	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_d	200	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	°C

Electrical Ratings @Ta=25°C

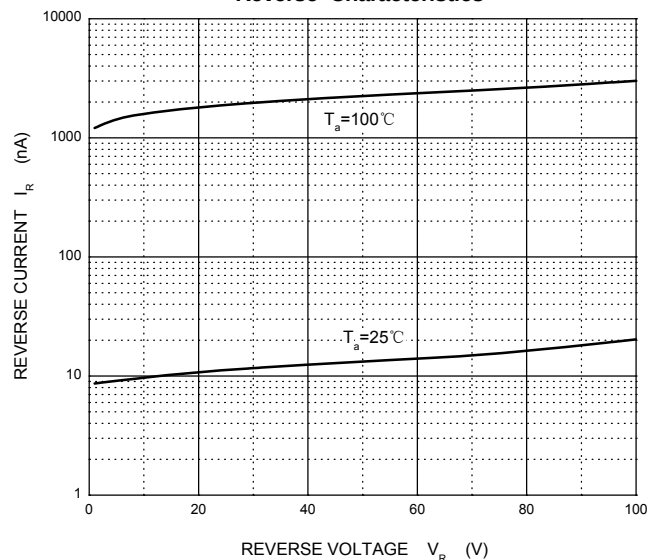
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	75			V	$I_R=10\mu A$
Forward Voltage	V_{F1}	0.62		0.72	V	$I_F=5mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse Current	I_{R1}			2.5	μA	$V_R=75V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance Between Terminals	C_T			4	pF	$V_R=0V, f=1MHz$
Reverse Recovery Time	t_{rr}			4	ns	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$

Typical Characteristics

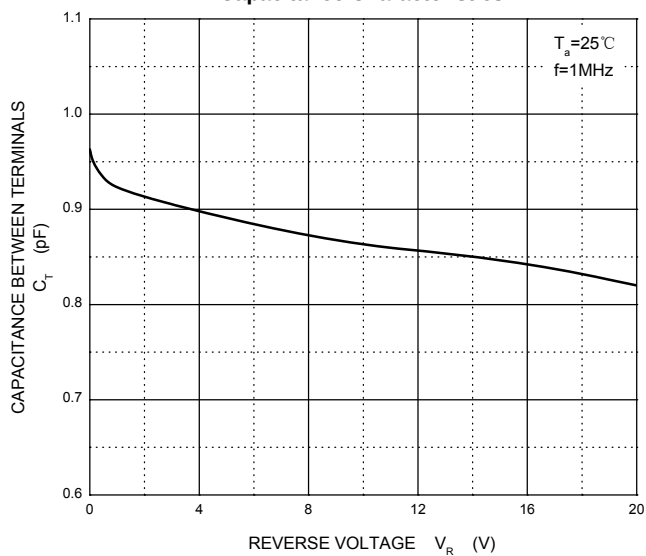
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

